

ANP series

ANP-1 supports pressureless bonding and is also compatible with Ni and Cu bonding.

Properties	ANP-1	ANP-8	Remarks
Viscosity	50~300Pa·s	50~300Pa·s	Adjustable
Sintering Temperature	250°C ↑ x300sec	300°C ↑ x300sec	May vary depending on equipment and sample conditions
Sintering Pressure	10MPa ↑	20MPa ↑	
Thermal conductivity (W/m·K)	330W/m·K	350W/m·K	
Shear Strength	40MPa	40MPa	
Target Metal	Ag,Au,Cu,Ni,Pd,Pt	Ag,Au,Cu,Ni,Pd,Pt	

ASTRO series

Enables pre-fixing after preliminary drying

ASTRO-HP	
Viscosity	10~100Pa·s
Sintering Temperature	250°C ↑ x300sec
Sintering Pressure	10MPa ↑
Thermal Conductivity (W/m·K)	330W/m·K
Shear Strength	30MPa
Target Metal	Ag,Au,Cu,Pd,Pt

ASTRO-LP	
Viscosity	10~100Pa·s
Sintering Temperature	220°C ↑ x300sec
Sintering Pressure	10MPa ↑
Thermal Conductivity (W/m·K)	350W/m·K
Shear Strength	20MPa
Target Metal	Ag,Au,Pd,Pt,(Cu)

Bonding at Lower Temperatures

ASTRO-MP	
Viscosity	10~100Pa·s
Sintering Temperature	230°C ↑ x300sec
Sintering Pressure	20MPa ↑
Thermal Conductivity (W/m·K)	Measuring
Shear Strength	30MPa
Target Metal	Ag,Au,Pd,Pt

For TIM Applications

For modules where grease or sheet materials are insufficient

Void-Free / Pressureless Bonding

ASTRO-LN	
Viscosity	10~300Pa·s
Sintering Temperature	250°C ↑ x60min
Sintering Pressure	0MPa
Thermal Conductivity (W/m·K)	155W/m·K
Shear Strength	20MPa
Target Metal	Ag,Au,Pd,Pt

For Die-Attach Applications

For Non-Pressurizable Devices

Optimal for bonding high-frequency amplifier chips and light-emitting devices which pressure cannot be applied

